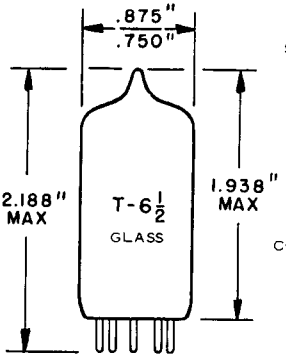
TUNG-SOL

PENTODE

MINIATURE TYPE

OUTLINE
JEDEC 6-2

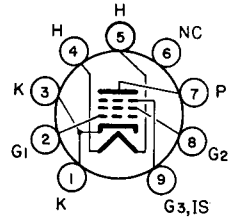


BASE 9 PIN BUTTON
JEDEC E9-1

SEMI-REMOTE-CUTOFF PENTODE
FOR
I.F. AMPLIFIER STAGES
IN TV RECEIVERS

COATED UNIPOTENTIAL CATHODE
ANY MOUNTING POSITION

BASING DIAGRAM
JEDEC 9PM



BOTTOM VIEW

THE 4JC6 IS A FRAME-GRID, SHARP-CUTOFF PENTODE IN THE 9 PIN MINIATURE CONSTRUCTION. IT IS DESIGNED FOR SERVICE IN THE IF AMPLIFIER STAGES OF TELEVISION RECEIVERS. EXCEPT FOR HEATER CHARACTERISTICS AND RATINGS, THE 4JC6 IS IDENTICAL TO THE 3JC6 AND THE 4JC6.

DIRECT INTERELECTRODE CAPACITANCES

WITHOUT EXTERNAL SHIELD

GRID 1 TO PLATE - MAX.	.019	pf
INPUT (G1 TO H + K + G3 + I.S. + G2)	8.2	pf
OUTPUT (P TO H + K + G3 + I.S. + G2)	3.0	pf

HEATER CHARACTERISTICS AND RATINGS

DESIGN MAXIMUM RATINGS - SEE EIA STANDARD RS-239

AVERAGE CHARACTERISTICS	4.5 VOLTS	450	mA
HEATER WARM-UP TIME		11	SECONDS
LIMITS OF SUPPLIED CURRENT		450 ± 30	mA
MAXIMUM HEATER-CATHODE VOLTAGE:			
HEATER NEGATIVE WITH RESPECT TO CATHODE			
TOTAL DC AND PEAK		200	VOLTS
HEATER POSITIVE WITH RESPECT TO CATHODE			
DC		100	VOLTS
TOTAL DC AND PEAK		200	VOLTS

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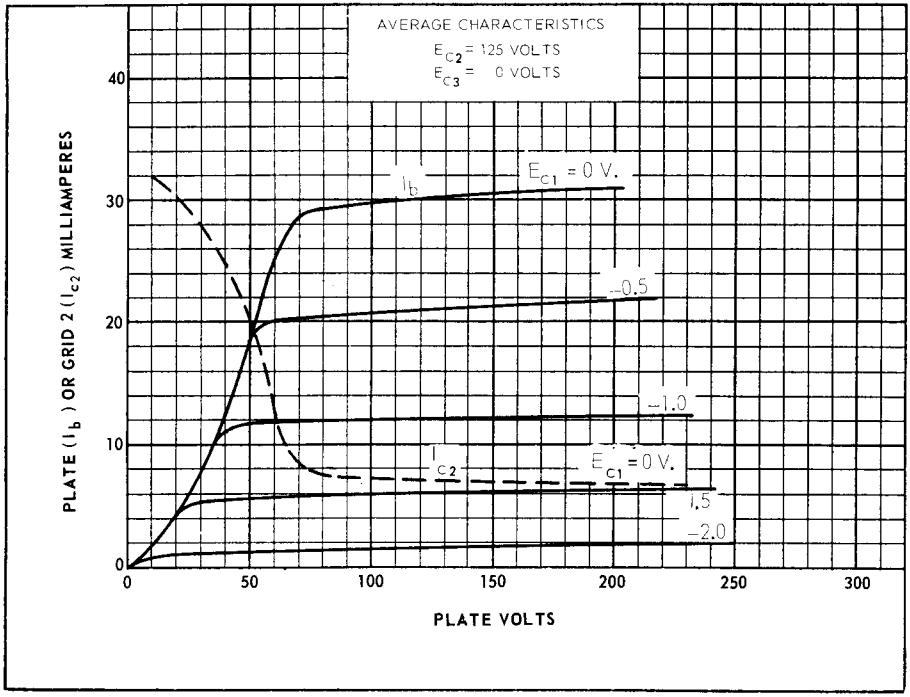
MAXIMUM RATINGS

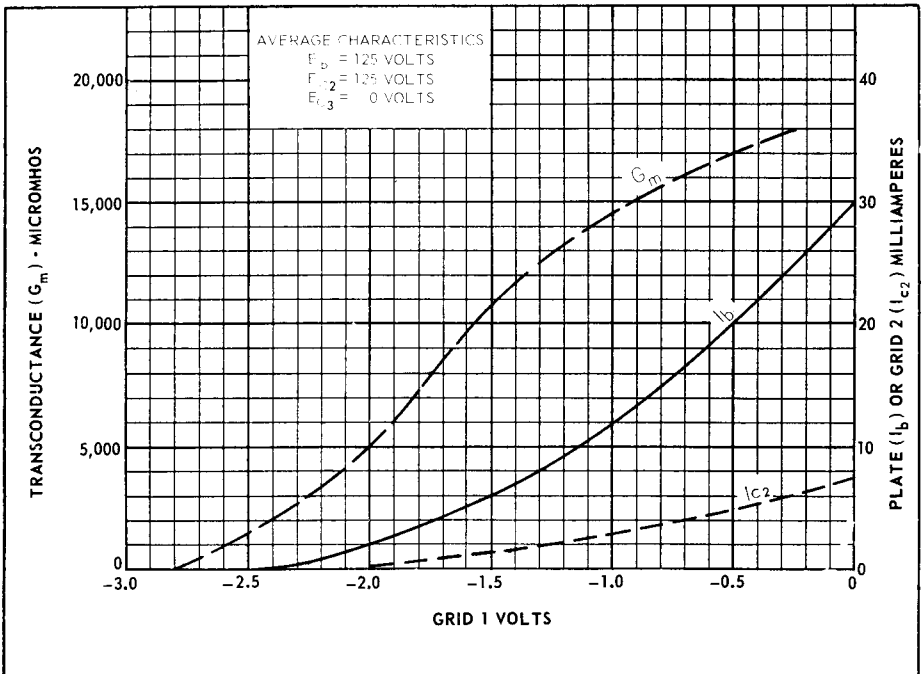
DESIGN MAXIMUM VALUES - SEE EIA STANDARD RS-239

PLATE VOLTAGE	330	VOLTS
GRID 2 SUPPLY VOLTAGE	330	VOLTS
GRID 2 VOLTAGE	See Rating Chart	
POSITIVE GRID 1 VOLTAGE	0	VOLTS
PLATE DISSIPATION	2.5	WATTS
GRID 2 DISSIPATION - UP TO 165 VOLTS	0.6	WATT
GRID 1 CIRCUIT RESISTANCES:		
CATHODE-BIAS RESISTOR	1	MEGOHM
FIXED BIAS	0.25	MEGOHM

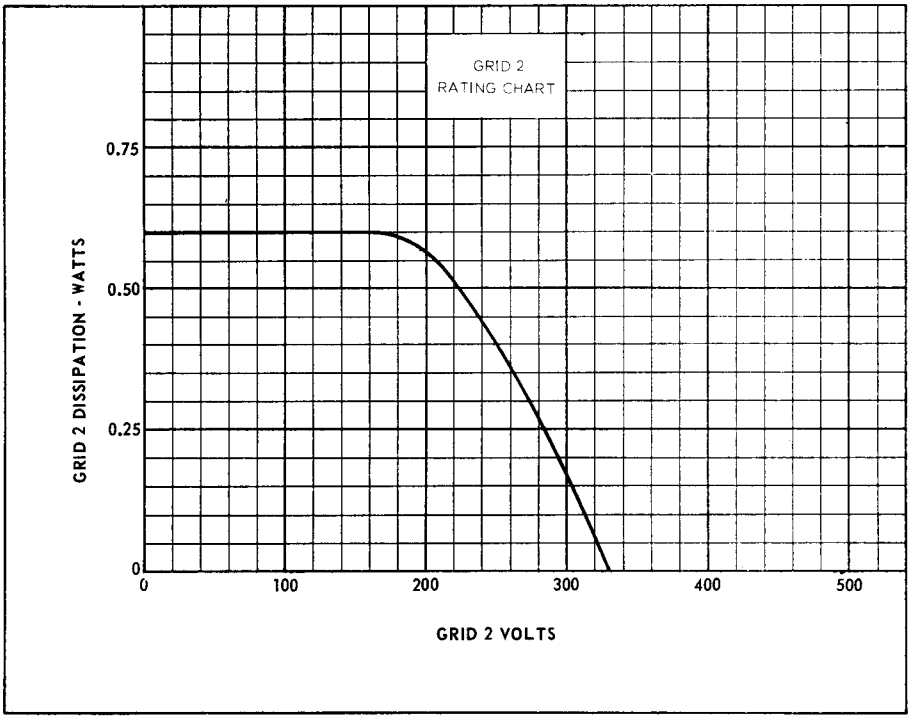
CHARACTERISTICS AND TYPICAL OPERATION

PLATE VOLTAGE	125	VOLTS
GRID 3 VOLTAGE	Connected To Cathode At Socket	
GRID 2 VOLTAGE	125	VOLTS
CATHODE-BIAS RESISTOR	56	OHMS
PLATE CURRENT	13	mA
GRID 2 CURRENT	3.2	mA
TRANSCONDUCTANCE	15,000	μMHOS
PLATE RESISTANCE	0.18	MEGOHM
GRID 1 VOLTAGE FOR I_b = 100 mA	-3.0	VOLTS


AVERAGE CHARACTERISTICS
E_{c_2} = 125 VOLTS
E_{c_3} = 0 VOLTS
I_b
E_{c_1} = 0 V.
-0.5
-1.0
I_{c_2}
E_{c_1} = 0 V.
-1.5
-2.0
PLATE (I_b) OR GRID 2 (I_{c_2}) MILLIAMPERES
PLATE VOLTS
0
10
20
30
40
0
50
100
150
200
250
300


AVERAGE CHARACTERISTICS
E_b = 125 VOLTS
E_{c_2} = 125 VOLTS
E_{c_3} = 0 VOLTS
G_m
I_b
I_{c_2}
TRANSCONDUCTANCE (G_m) - MICROMHOS
PLATE (I_b) OR GRID 2 (I_{c_2}) MILLIAMPERES
GRID 1 VOLTS
0
5,000
10,000
15,000
20,000
0
10
20
30
40
-3.0
-2.5
-2.0
-1.5
-1.0
-0.5
0

4JC6


GRID 2
RATING CHART
GRID 2 DISSIPATION - WATTS
0.75
0.50
0.25
0
0
100
200
300
400
500
GRID 2 VOLTS